

*Concld  
C1  
B1  
encl*

of said cathode material; and

an emitting layer over each of said at least one tip, wherein said emitting layer is comprised of a metal silicide and has a thickness between 50 and 3000 angstroms.

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Please REWRITE claim 39 as follows:

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*sub  
C1  
B1*

39. (AMENDED) A large area passive matrix cold cathode field emission display device comprising:

cathode material on a semiconductor substrate;

at least one emitter tip with a sharp profile for emitting electrons formed out of said cathode material;

an emitting layer over each of said at least one tip, wherein said emitting layer is comprised of a metal silicide and has a thickness between 50 and 3000 angstroms.

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